EE

MICROWAVE MEASUREMENTS

Chairman: Stephen F. Adam—Adam Microwave Consulting

Session Abstract: The measurement of memory effects in predistortion linearizers is discussed in circuits as they apply to AM/AM and AM/PM characteristics. A picosecond optoelectronic characterization of a heterojunction bipolar transistor is presented and compared to on-wafer, Network Analyzer Probing. A noise characterization paper enumerates uncertainties of microwave devices such as GaAs MESFETs and psuedomorphic MODFETS operating at low currents, such as I_{ds} less than 1 mA. Another paper deals with heterojunction bipolar transistor parameter extraction techniques at millimeter-wave frequencies through some unique de-embedding process. NIST (formerly NBS) describes a very accurate method of calibrating and measuring dielectric properties of materials. Finally a novel approach is described to make fluid thickness measurements in a microstrip with a non-contacting process.

8:30 a.m.–10:00 a.m., Thursday, June 15, 1989
Center Theater